Jan Kopaczek

List of Publications by Year in descending order

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687363 794594 19 464 13 19 citations h-index g-index papers 19 19 19 516 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	High Bi content GaSbBi alloys. Journal of Applied Physics, 2014, 116, .	2.5	70
2	Pressure coefficients for direct optical transitions in MoS2, MoSe2, WS2, and WSe2 crystals and semiconductor to metal transitions. Scientific Reports, 2016, 6, 26663.	3.3	56
3	Theoretical and experimental studies of electronic band structure for GaSb1â^'xBix in the dilute Bi regime. Journal Physics D: Applied Physics, 2014, 47, 355107.	2.8	50
4	Temperature dependence of the band gap of GaSb1â^'xBix alloys with O < x â‰ æ €‰0.042 dephotoreflectance. Applied Physics Letters, 2013, 103, .	etermined	by 46
5	Direct optical transitions at K- and H-point of Brillouin zone in bulk MoS2, MoSe2, WS2, and WSe2. Journal of Applied Physics, 2016, 119, .	2.5	46
6	Contactless electroreflectance study of E0 and E0 + ΔSO transitions in In0.53Ga0.47BixAs1â^2 alloys. Applied Physics Letters, 2011, 99, 251906.	3.3	33
7	Optical properties of GaAsBi/GaAs quantum wells: Photoreflectance, photoluminescence and time-resolved photoluminescence study. Semiconductor Science and Technology, 2015, 30, 094005.	2.0	30
8	Unusual broadening of E0 and E0 + \hat{i} "SO transitions in GaAsBi studied by electromodulation spectroscopy. Journal of Applied Physics, 2012, 111, 066103.	2.5	20
9	Direct and indirect optical transitions in bulk and atomically thin MoS2 studied by photoreflectance and photoacoustic spectroscopy. Journal of Applied Physics, 2019, 125, .	2.5	17
10	Hidden spin-polarized bands in semiconducting 2H-MoTe ₂ . Materials Research Letters, 2020, 8, 75-81.	8.7	17
11	Type I GaSb1-xBix/GaSb quantum wells dedicated for mid infrared laser applications: Photoreflectance studies of bandgap alignment. Journal of Applied Physics, 2019, 125, .	2.5	16
12	Temperature Dependence of the Indirect Gap and the Direct Optical Transitions at the High-Symmetry Point of the Brillouin Zone and Band Nesting in MoS ₂ , MoSe ₂ , MoTe ₂ , WS ₂ , and WSe ₂ Crystals. Journal of Physical Chemistry C, 2022, 126, 5665-5674.	3.1	16
13	Structural and optical properties of GaSbBi/GaSb quantum wells [Invited]. Optical Materials Express, 2018, 8, 893.	3.0	15
14	Experimental and Theoretical Studies of the Electronic Band Structure of Bulk and Atomically Thin Mo _{1–<i>x</i>} W <i>_x</i> Se ₂ Alloys. ACS Omega, 2021, 6, 19893-19900.	. 3.5	9
15	Bowing of the band gap and spin-orbit splitting energy in BGaAs. Materials Research Express, 2019, 6, 125913.	1.6	8
16	Strong Substrate Strain Effects in Multilayered WS ₂ Revealed by High-Pressure Optical Measurements. ACS Applied Materials & Description (1988) amp; Interfaces, 2022, , .	8.0	8
17	Optical properties and dynamics of excitons in Ga(Sb, Bi)/GaSb quantum wells: evidence for a regular alloy behavior. Semiconductor Science and Technology, 2020, 35, 025024.	2.0	3
18	Photoreflectance studies of temperature and hydrostatic pressure dependencies of direct optical transitions in BGaAs alloys grown on GaP. Journal Physics D: Applied Physics, 2022, 55, 015107.	2.8	3

Optical spectroscopy studies of atom intermixing in the core versus growth temperature of the claddings in MOCVD-grown quantum cascade lasers. Journal of Physics Communications, 2019, 3, 1.2 1 125007.	#	Article	IF	CITATIONS
	19		1.2	1